

ECE 3150 Homework #5 Solutions
(Farhan Rana)

S.1

a) We need to have no current going through the resistor. So

$$-I_D = \frac{k_p}{2} (V_{IN} - V_{DD} - V_{TP})^2 (1 - \lambda_p (V_{OUT} - V_{DD})) = I_{BIAS} = 100 \mu A$$

$$\Rightarrow (250 \mu A/V^2) (V_{IN} - 2)^2 (1 + \lambda_p (2.5)) = 100 \mu A$$

$$\Rightarrow V_{IN} = 1.417 \text{ Volts}$$

Check: Since $V_{DS} = V_{OUT} - V_{DD} = -2.5 V < V_{GS} - V_{TP} = V_{IN} - V_{DD} - V_{TP} = -0.585$
the FET is in saturation.

b)



c) $A_v = -g_m (r_o \parallel R_L)$

$$g_m = \frac{\partial I_D}{\partial V_{GS}} = -k_p (V_{IN} - V_{DD} - V_{TP}) (1 + \lambda_p V_{DD}) = +3.4 \times 10^{-4} A/V$$

$$g_o = \frac{1}{r_o} = \frac{\partial I_D}{\partial V_{DS}} = \frac{k_p}{2} (V_{IN} - V_{DD} - V_{TP})^2 \lambda_p = 5.74 \times 10^{-6} S$$

$$\Rightarrow r_o = 1.74 \times 10^5 \Omega$$

$$\Rightarrow (r_o \parallel R_L) = 9.46 \times 10^3 \Omega$$

$$\Rightarrow A_v = -3.21$$

d) PMOS will remain in saturation provided:

e) $V_{DS} < V_{GS} - V_{TP}$ and $V_{GS} < V_{TP}$

$$\Rightarrow V_{IN} - V_{DD} < V_{TP}$$

$$\Rightarrow V_{IN} < 2.0$$

We also have

$$V_{OUT} = (-I_D - I_{BIAS}) R_L$$

$$\Rightarrow \frac{V_{OUT}}{R_L} + I_{BIAS} = -I_D = \frac{k_p}{2} (V_{IN} - V_{DD} - V_{TP})^2 (1 - \lambda_p (V_{OUT} - V_{DD}))$$

$$\Rightarrow \frac{\frac{V_{OUT}}{R_L} + I_{BIAS}}{1 - \lambda_p (V_{OUT} - V_{DD})} = \frac{k_p}{2} (V_{IN} - V_{DD} - V_{TP})^2 \quad \text{--- (1)}$$

The above equation can be used to figure out V_{OUT} for every V_{IN} provided the PFET is in saturation, which would be the case provided $V_{DS} < V_{GS} - V_{TP}$

$$\Rightarrow V_{OUT} < V_{IN} + 0.5 \quad \text{--- (2)}$$

and provided $V_{GS} < V_{TP}$

$$\Rightarrow V_{IN} < 2.0$$

One can plot V_{OUT} vs V_{IN} using eq. (1) and also plot

$V_{OUT} = V_{IN} + 0.5$ {eq. (2)}. The portion of curve of eq. (1) below

eq. (2) curve will give the range of values for V_{OUT} and

V_{IN} for which the PFET will be in saturation. The graph

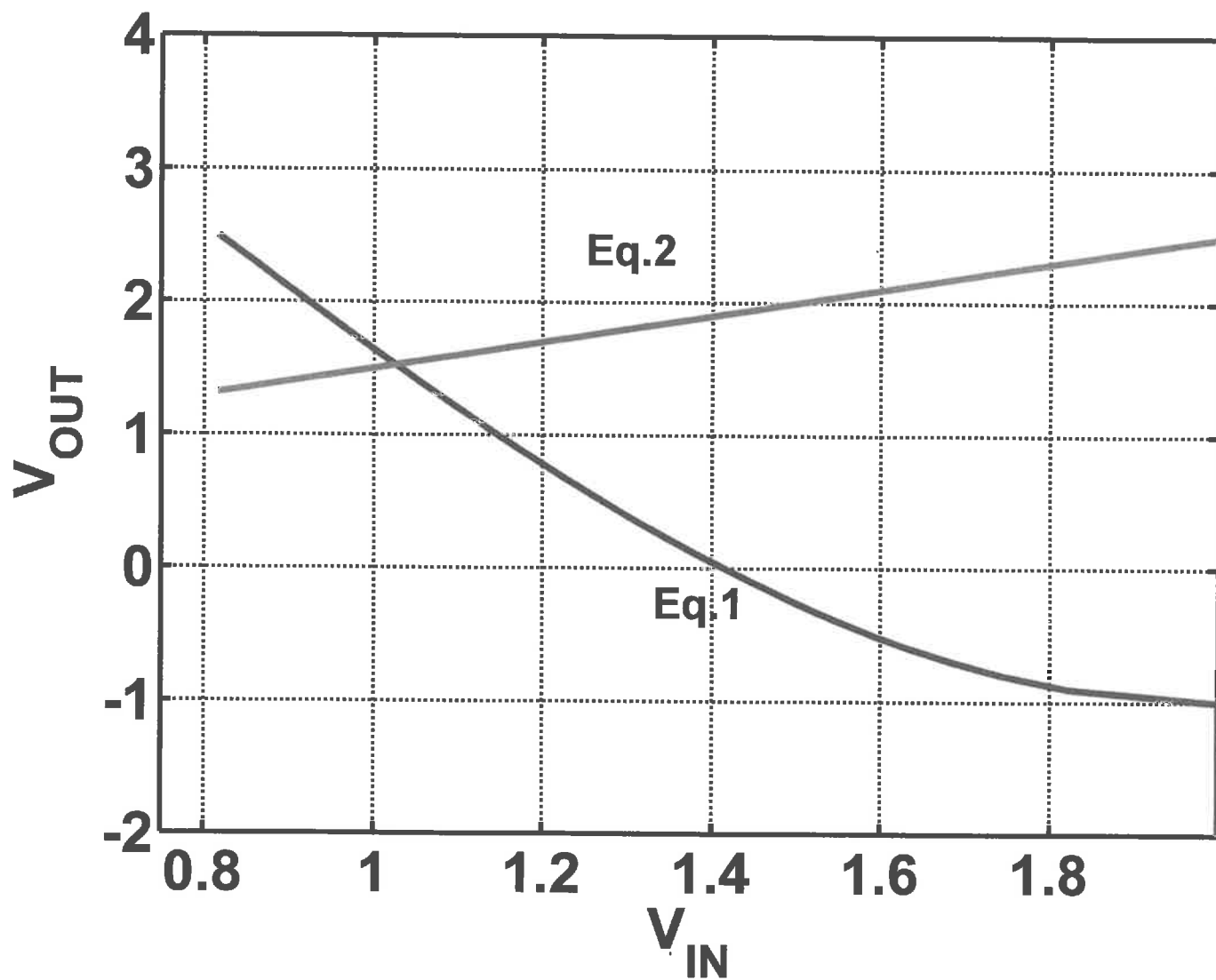
is plotted on the next page.

$$V_{OUT}|_{max} = +1.526 \text{ V}$$

$$V_{OUT}|_{min} = -1 \text{ V}$$

$$V_{IN}|_{max} = +2.0 \text{ V}$$

$$V_{IN}|_{min} = 1.026 \text{ V}$$



5.2

a) $V_{DS-sat} = V_{GS} - V_{TN} = 4 - 1 = 3 \text{ V}$

b) $I_D = \frac{W}{2L} \mu_n C_{ox} (V_{GS} - V_{TN})^2 = 2 \text{ mA}$ for $V_{GS} - V_{TN} = 3 \text{ V}$

$\Rightarrow \mu_n = 515 \frac{\text{cm}^2}{\text{V}\cdot\text{s}}$

c) $Q_N = -C_{ox} (V_{GS} - V_{TN}) = -10^{-6} \text{ C/cm}^2$

d) $Q_N = -C_{ox} (V_{GS} - V_{TN} - V_{DS}) = -0.6 \times 10^{-6} \text{ C/cm}^2$

e) $I_D = -W Q_N V_{dn} = 2 \times 10^{-3} \text{ A}$ $\left\{ Q_N = -10^{-6} \text{ C/cm}^2 \right\}$ source end

$\Rightarrow V_{dn} = 8 \times 10^5 \text{ cm/s}$

f) $I_D = -W Q_N V_{dn} = 2 \times 10^{-3} \text{ A}$ $\left\{ Q_N = -0.6 \times 10^{-6} \text{ C/cm}^2 \right\}$ drain end

$\Rightarrow V_{dn} = 1.33 \times 10^6 \text{ cm/s}$

g) $Q_N = -C_{ox} (V_{GS} - V_{TN}) = -10^{-6} \text{ C/cm}^2$

h) $Q_N = -C_{ox} (V_{GS} - V_{TN} - V_{DS})$ will give a positive inversion layer

density at the drain which is nonsense. The device is in saturation and the channel near the drain end has been pinched off. Therefore, $Q_N \approx 0$

i) $V_{TN} = V_{TN}(V_{SB}=0) + \gamma_n \left[\sqrt{-2\phi_p + V_{SB}} - \sqrt{-2\phi_p} \right]$

$\phi_p = -0.416$ $\gamma_n = \frac{\sqrt{2\epsilon_s q N_A}}{C_{ox}} = 0.527 \sqrt{\text{V}}$

$\Rightarrow V_{TN} = 1 + 0.79 = 1.79 \text{ V} \Rightarrow I_D = 1.1 \text{ mA}$